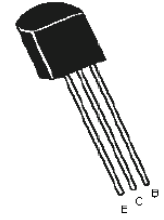


Bipolar Transistor



Pin Configuration:

1. Emitter
2. Collector
3. Base

Description:

- NPN Silicon Planar Epitaxial Transistor

Absolute Maximum Ratings

Rating	Symbol	Value	Unit
Collector Emitter Voltage	V_{CEO}	30	V
Collector Base Voltage	V_{CBO}	50	
Emitter Base Voltage	V_{EBO}	5	
Collector Current Continuous	I_C	600	mA
Power Dissipation at $T_a = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$

Thermal Resistance

Junction to Ambient	$R_{th(j-a)}$	200	$^\circ\text{C/W}$
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Electrical Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Test Condition	Min.	Max.	Unit
Collector Emitter Voltage	BV_{CEO}^*	$I_C = 10\text{mA}, I_B = 0$	30	-	V
Collector Base Voltage	BV_{CBO}	$I_C = 100\mu\text{A}, I_E = 0$	50	-	
Emitter to Base Voltage	V_{EBO}	$I_E = 100\mu\text{A}, I_C = 0$	5	-	
DC Current Gain 2N3704	h_{FE}^*	$I_C = 50\text{mA}, V_{CE} = 2\text{V}$	100	300	-
Collector Leakage Current	I_{CBO}	$V_{CB} = 20\text{V}, I_E = 0$	-	0.1	μA

*Pulse Test : Pulse Width = $\leq 300\mu\text{s}$, Duty Cycle = $\leq 2.0\%$.

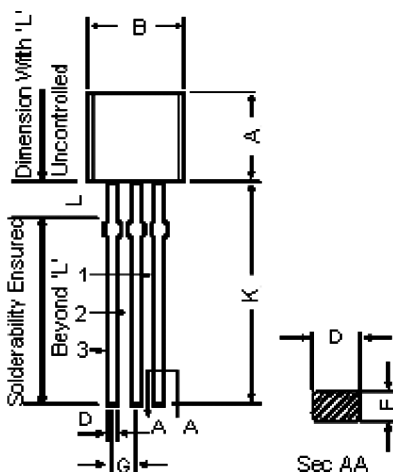
Electrical Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristic	Symbol	Test Condition	Min.	Max.	Unit
Emitter Leakage Current	I_{EBO}	$V_{EB} = 3V, I_C = 0$	-	0.1	μA
Collector Emitter Saturation Voltage 2N3704	$V_{CE(sat)}^*$	$I_C = 100\text{mA}, I_B = 5\text{mA}$	-	0.6	V
Base Emitter On Voltage	$V_{BE(on)}^*$	$I_C = 100\text{mA}, V_{CE} = 2V$	0.5	1	

Small Signal Characteristics

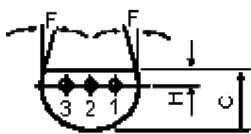
Output Capacitance	C_{ob}	$I_E = 0, V_{CB} = 10V, f = 1\text{MHz}$	-	12	pF
Transition Frequency	f_T	$I_C = 50\text{mA}, V_{CE} = 2V, f = 20\text{MHz}$	100	-	MHz

*Pulse Test : Pulse Width = $\leq 300\mu\text{s}$, Duty Cycle = $\leq 2.0\%$.



Dimensions	Min.	Max.
A	4.32	5.33
B	4.45	5.2
C	3.18	4.19
D	0.41	0.55
E	0.35	0.5
F	5°	
G	1.14	1.4
H		1.53
K	12.7	-
L	1.982	2.082

Dimensions : Millimetres



Part Number Table

Description	Part Number
Transistor, NPN, TO-92	2N3704

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